Shanghai Fudan Microelectronics Group Company Limited

上海复旦微电子集团股份有限公司
Shanghai Fudan Microelectronics Group Company Limited

FM11NT021TT

NFC Forum Type2 Tag compliant IC with 144 bytes user memory and Open Sense function

Datasheet

Nov. 2022

Contents

1 Product Overview

1.1 Introduction

FM11NT021TT is primarily designed for NFC Forum Type 2 Tag applications. Please consult Fudan Microelectronics Company for more documents.

1.2 Features

1.2.1 RF Interface

- ISO/IEC 14443A
- Contactless transmission of data and supply energy (no battery needed)
- Operating distance: up to 100 mm (depending on various parameters as e.g. field strength and antenna geometry)
- Operating frequency: 13.56 MHz
- Fast data transfer: 106 Kbit/s
- High data integrity: 16-bit CRC, parity, bit coding, bit counting
- 7 byte UID (cascade level 2 according to ISO/IEC 14443-3)
- Fast read command
- Read times counter function
- Open sense function (Tamper detection)

1.2.2 EEPROM

- user memory: 144 bytes (36 pages)
- 4 bytes initialized capability container with one time programmable access bits
- Field programmable read-only locking function per page for the first 16 pages
- Field programmable read-only locking function above the first 16 pages per double page
- Data retention of 10 years
- Write endurance 500,000 cycles

1.2.3 NFC Forum Tag 2 Type compliance

FM11NT021TT provides full compliance to the NFC Forum Type 2 Tag technical specification and enables NDEF data structure configuration.

1.2.4 Security

- Manufacturer programmed 7-byte UID for each chip
- Anti-tearing support for capability container (CC) and lock bits
- Field programmable read-only locking function

1.3 Block Diagram
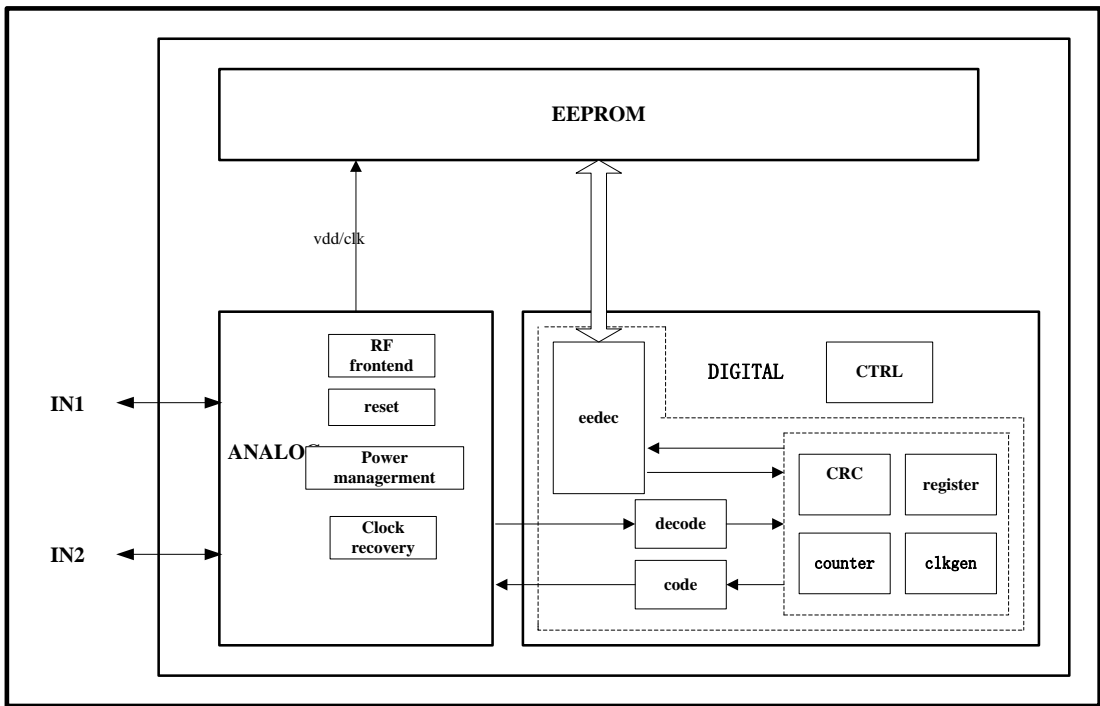
Figure 1-1 FM11NT021TT Block diagram

1.4 Bumping Pin Description
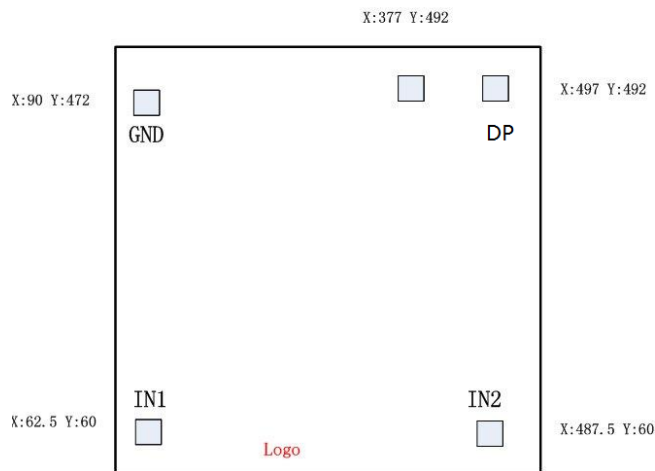
Figure 1-2 FM11NT021TT Bumping Pin Description

Number	Bumping pin name	Description
1	GND	Ground pin
2	DP	Detection Pad, Connecting with the GND pad
3	IN2	Antenna Connection
4	IN1	Antenna Connection

2   Functional Description

2.1   General Description

FM11NT021TT chip has an 180bytes EEPROM memory embedded. FM11NT021TT contains the RF-Interface and the Digital Control Unit. Energy and data are transferred via an antenna, which consists of a coil with a few turns directly connected to the IN1 and IN2 of the FM11NT021TT.

FM11NT021TT has a dedicated function which is named open sense or tamper detection. A wire connects the DP pad and the GND pad when the tag is made. If this wire is open, the chip can detect this state and send this message to the reader when being checked. This function can be used in applications such as anti-counterfeit or smart packages.

2.2   Memory Organization

• EEPROM: 180 bytes, organized in 45 pages of 4 byte per page.

– 26 bytes reserved for manufacturer and configuration data

– 34 bits used for the read-only locking mechanism

– 4 bytes available as capability container

– 144 bytes user programmable read/write memory

Table 2-1 FM11NT021TT Memory organization

Page No		Byte Number inside a page			
DEC	HEX	0	1	2	3
0	0h	Serial Number			
1	1h	Serial Number			
2	2h	Serial Number	Internal	Lock Byte	Lock Byte
3	3h	Capability Container (CC)			
4	4h	TLV			
5	5h				
...	...	Static Data Area (Page4-15)			
15	Fh				
16	10h	Dynamic Data Area (Page 16-39, total 24blocks)			
...	...				
40	28h	Dynamic Lock Bytes			
41	29h	RFU			
42	2Ah				
43	2Bh				
44	2Ch				

2.2.1 UID

The unique 7 byte serial number (UID) and its two Block Check Character Bytes (BCC) are programmed into the first 9 bytes of the memory. It therefore covers page 00h, page 01h and the first byte of page 02h. The second byte of page 02h is reserved for internal data. Due to security and system requirements these bytes are write-protected after the programming during the IC production.

According to ISO/IEC 14443-3, BCC0 is defined as CT SN0 SN1 SN2. An ABBREVIATION CT stays for Cascade Tag byte (88h) and BCC1 is defined as SN3 SN4 SN5 SN6. SN0 holds the Manufacturer ID for Fudan Microelectronics (1Dh) according to ISO/IEC 14443-3 and ISO/IEC 7816-6 AMD.1.

2.2.2 Lock bytes

Lock bytes enable the user to lock parts of the complete memory area for writing. A Read from user memory area cannot be restricted via lock bytes functionality. The lock bytes functionality is enabled with a WRITE command, where 2 out of 4 bytes transmitted are used for setting the lock bytes.

2.2.2.1 Static Lock

The bits of byte 2 and byte 3 of page 02h represent the field programmable read-only locking

mechanism. Each page from 03h (CC) to 0Fh can be individually locked by setting the

corresponding locking bit Lx to logic 1 to prevent further write access. After locked, the corresponding page becomes read-only memory.

The three least significant bits of lock byte 0 are the block-locking bits. Bit 2 deals with pages 0Ah to 0Fh, bit 1 deals with pages 04h to 09h and bit 0 deals with page 03h (CC). Once the block-locking bits are set, the locking configuration for the corresponding memory area is frozen.

Table 2-2 Lock0（Block 02，Byte2）

BIT	7 （MSB）	6	5	4	3	2	1	0 （LSB）
Locked Block Number （Decimal）	7	6	5	4	CC	BL 15~10	BL 9~4	BL CC

Table 2-3 Lock1（Block 02，Byte3）

BIT	7 （MSB）	6	5	4	3	2	1	0 （LSB）
Locked Block Number （Decimal）	15	14	13	12	11	10	9	8

For example if BL15-10 is set to logic 1, then bits L15 to L10 (lock byte 1, bit [7:2]) can no longer be changed. The so called static locking and block-locking bits are set by a WRITE command to page 02h. Bytes 2 and 3 of the WRITE command and the contents of the lock bytes are bit-wise OR'ed and the result then becomes the new content of the lock bytes. This process is irreversible. If a bit is set to logic 1, it cannot be changed back to logic 0. The contents of bytes 0 and 1 of page 02h are unaffected by the corresponding data bytes of the WRITE command. The default value of the static lock bytes is 0000h. Any write operation to the static lock bytes is tearing-proof.

2.2.2.2　Dynamic Lock

The dynamic lock bytes are used to lock the pages starting at page address 10h.
The lock bytes are located at page 28h. The three lock bytes cover the memory area of 96 data bytes for FM11NT021TT. The granularity is 2 pages.

The default value of the dynamic lock bytes is 00 00 00h. The value of Byte 3 is always BDh when read. Any write operation to the dynamic lock bytes is tearing-proof.

2.2.3　CC bytes

The Capability Container CC (page 3) is programmed according to the NFC Forum Type 2 Tag specification Ref. 8. You can change these bytes by a WRITE command.

The content that needs to be written in will be OR'ed with the current contents of the CC bytes. The result will replace the old contents in CC area. This process is irreversible. If a bit is set to "1", it cannot be changed back to "0" again.

2.2.4 Initial memory configuration

The page 03h, 04h and 05h of FM11NT021TT are initialized according to the NFC Forum Type 2 Tag specification.

Table 2-4 Initial memory organization of FM11NT021TT

Page Address	Byte0	Byte1	Byte2	Byte3
03h	E1h	10h	12h	00h
04h	01h	03h	A0h	0Ch
05h	34h	03h	00h	FEh

2.2.5 Configuration block

2.2.5.1 Overview

FM11NT021TT's 29h~2Ch store the configuration information：

Table 2-5 Configuration area

Page address	Byte0	Byte1	Byte2	Byte3
29h	TT_CONF	RFUI	TT _ADDR	AUTH0
2Ah	ACCESS	RFUI	RFUI	RFUI
2Bh	PWD			
2Ch	PACK		RFUI	RFUI

2.2.5.2 TT_CONF

Table 2-6 TT_CONF byte

Name：TT_CONF			
Field	**Description**	**Reset**	**Access**
7:6	TT function Enable 11:TT_EN 00: RFU 01: RFU 10: RFU	00	RW
5:0	RFU	0	RW

2.2.5.3   TT_ADDR

Table 2-7 TT_ADDR byte

Name：TT_ADDR			
Field	**Description**	**Reset**	**Access**
7:0	TT_ Address Definition of the start page address of open sense information	00	RW

2.2.5.4   ACCESS

Table 2-8 Access byte

Name：ACCESS			
Field	**Description**	**Reset**	**Access**
7	PROT Definition of what will be protected by the password 0：Write operation need password check firstly 1：Write and read operation all need password check firstly	0	RW
6	CFGLOCK The lock bits of the configuration area（only lock the lowest 2 pages） 0：The configuration area can be changed 1：The configuration area cannot be changed permanently	0	RW
5	RFU		
4	NFC_CNT_EN 0：Counter function is disabled 1：Counter function is enabled	0	RW
3	NFC_CNT_PWD_PROT 0：Counter function is not protected by the password 1：Counter function is under the protection of the password	0	RW
2:0	AUTHLIM The up limit of the password check error times 000：no limit 001-111：the maximum times of the check error	3'b000	RW

2.2.5.5   AUTH0

Table 2-9 AUTH0

Name：AUTH0			
Field	**Description**	**Reset**	**Access**
7:0	AUTH0 Definition of the start page address which need to be protected	8'hFF	RW

	by the password		

2.2.5.6 PWD

Table 2-10 PWD

Name：PWD			
Field	**Description**	**Reset**	**Access**
31:0	PWD 32bits password, unreadable in the user mode It is recommended to set the PWD under the protection of AUTH0	32'hFFFFFFFF	RW

2.2.5.7 PACK

Table 2-11 PACK Byte

Name：PACK			
Field	**Description**	**Reset**	**Access**
15:0	PACK The response of password verification PACK will be sent back when the password in PWD_AUTH command is the same to the stored password. Otherwise, NAK will be sent back. It is recommended to set the PACK under the protection of AUTH0.	16'h0000	RW

2.3   Special Function

2.3.1   Read times counter

FM11NT021TT has a read times counter function. Once the tag is read by the READ command or FAST-READ command, the 24bits counter's value will be added automatically.
This function can be enabled or disabled with the NFC_CNT_EN bit. The actual counter value can be read by READ_CNT command or Counter mapping feature.
The reading of the Counter can also be protected with the password authentication. The Counter password protection is enabled or disabled with the NFC_CNT_PWD_PROT bit.

2.3.2   Password protection

The read and write authority to the specific address of the memory can be controlled by the password which stored in the EEPROM (4bytes). The response which is 2 bytes is also stored in the EEPROM. User can change them all by themselves.
AUTHLIM is used to define the up limit of the failed password check times. If the error times is out of the limit value, the chip will not response to the check request anymore.

AUTH0's default value is FFh that main the password protection function has been shutdown. User can turn it on after the confiuration. The memory of EEPROM will be protected by the password whose address is startting from the AUTH0.

2.3.3 Open sense function

FM11NT021TT has the open sense function that can detect the open or short state of the wire connecting the DP pad and the GND pad. The reader or the smart phone with NFC reader function can use the normal read command to detect the wire's state.
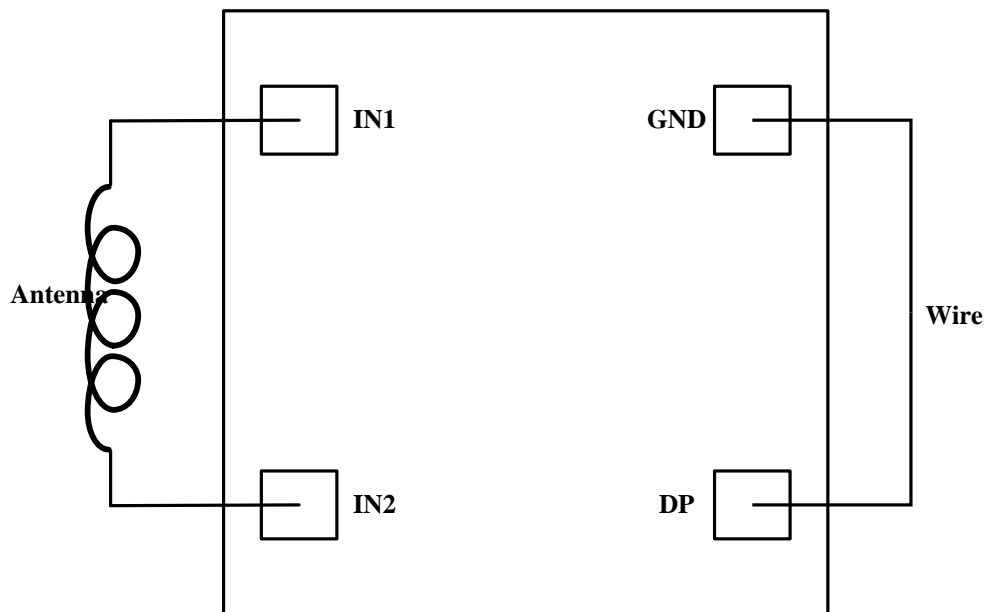
The chip needs to be configured as below to enable the Open Sense function:
- TT_EN = 2'b11，This setting is to enable the Open Sense function.
- TT_ADDR should be configured and TT_ADDR must be greater than 0x03.

The open or short information must use READ command to read out. The READ command address is TT_ADDR, and 16 bytes data is returned, the 15th byte represents the open or short state, if the symbol is 79H, that means the wire is opened, otherwise, 78H means connected.

2.4   Command set

FM11NT021TT's command is following ISO/IEC14443-A.

Table 2-12 Command overviews

Command	Command code (hexadecimal)

Request	26h (7 bit)
Wake-up	52h (7 bit)
Anticollision CL1	93h 20h
Select CL1	93h 70h
Anticollision CL2	95h 20h
Select CL2	95h 70h
Halt	50h 00h
READ	30h
FAST_READ	3Ah
WRITE	A2h
READ_CNT	39h
PWD_AUTH	1Bh

2.4.1 READ

The READ command is used to read 16bytes data from the memory of FM11NT021TT at a time. The data is the 4 pages that start from the address in the command's parameter.

Table 2-13 READ command

Name	Code	Description	Length
Cmd	30h	read four pages	1 byte
Addr	-	start page address	1 byte
CRC	-	CRC according to ISO/IEC14443	2 bytes
Data	-	Data content of the addressed pages	16 bytes
NAK	see Table 2-23	see Section 2.4.3	4-bit

The timing is according to ISO/IEC 14443-3 frame specification.

Table 2-14 READ timing

	$T_{ACK/NAK}$ min	$T_{ACK/NAK}$ max	$T_{TimeOut}$
READ	n=9	$T_{TimeOut}$	5 ms

2.4.2 FAST_READ

The FAST_READ command is used to read more than 16bytes data quickly. The data is all of the pages between the start address and the end address.

Table 2-15 FAST_READ command

Name	Code	Description	Length

Cmd	3Ah	read multiple pages	1 byte
StartAddr	-	start page address	1 byte
EndAddr	-	end page address	1 byte
CRC	-	CRC according to ISO/IEC14443	2 bytes
Data	-	data content of the addressed pages	n*4 bytes
NAK	see Table 2-23	see Section 2.4.3	4-bit

The timing is according to ISO/IEC 14443-3 frame specification.

Table 2-16 FAST_READ timing

	$T_{ACK/NAK}$ min	$T_{ACK/NAK}$ max	$T_{TimeOut}$
FAST_READ	n=9	$T_{TimeOut}$	5 ms

2.4.3   WRITE

The WRITE command is used to writes 4 bytes of data into the addressed FM11NT021TT's page.

Table 2-17 WRITE command

Name	Code	Description	Length
Cmd	A2h	write one page	1 byte
Addr	-	page address	1 byte
CRC	-	CRC according to ISO/IEC14443	2 bytes
Data	-	data	4 bytes
NAK	see Table 2-23	see Section 2.4.3	4-bit

The timing is according to ISO/IEC 14443-3 frame specification.

Table 2-18 WRITE timing

	$T_{ACK/NAK}$ min	$T_{ACK/NAK}$ max	$T_{TimeOut}$
FAST_READ	n=9	$T_{TimeOut}$	5 ms

2.4.4 READ_CNT

The READ_CNT command is used to read out the current value of the 24 bits counter.

Table 2-19 READ_CNT command

Name	Code	Description	Length
Cmd	39h	read counter	1 byte
Addr	02h	page address	1 byte
CRC	-	CRC according to ISO/IEC14443	2 bytes
Data	-	counter value	3 bytes
NAK	see Table 2-23	see Section 2.4.3	4-bit

The timing is according to ISO/IEC 14443-3 frame specification.

Table 2-20 READ_CNT timing

	$T_{ACK/NAK}$ min	$T_{ACK/NAK}$ max	$T_{TimeOut}$
READ_CNT	n=9	$T_{TimeOut}$	5 ms

2.4.5   PWD_AUTH

PWD_AUTH is used to check the password which protects the area defined by AUTH0.

Table 2-21 PWD_AUTH command

Name	Code	Description	Length
Cmd	1Bh	password authentication	1 byte
Addr	-	password	4 bytes
CRC	-	CRC according to ISO/IEC14443	2 bytes
Data	-	password authentication acknowledge	2 bytes
NAK	see Table 2-23	see Section 2.4.3	4-bit

The timing is according to ISO/IEC 14443-3 frame specification.

Table 2-22 PWD_AUTH timing

	$T_{ACK/NAK}$ min	$T_{ACK/NAK}$ max	$T_{TimeOut}$
READ_CNT	n=9	$T_{TimeOut}$	5 ms

2.4.6   ACK and NAK

FM11NT021TT uses a 4 bit ACK / NAK:

Table 2-23 ACK and NAK values

Code (4-bit)	ACK/NAK

Ah	Acknowledge (ACK)
0h	NAK for invalid argument (i.e. invalid page address)
1h	NAK for parity or CRC error
4h	NAK for invalid authentication counter overflow
5h	NAK for EEPROM write error

FM11NT021TT replies to a Select CL2 command with 44h which is transmitted with the least significant byte first.

3 Characteristics

3.1 Limiting values

Parameter		Min	Max	Unit
storage temperature		-55	+125	°C
input current（IN1 to IN2）		-	± 30	mA
ESD (HBM)）	【2】	-	± 4	KV

Table 3-1 FM11NT021TT Limiting values【1】

【1】Stresses above one or more of the limiting values may cause permanent damage to the device.

【2】Human body model: C = 100 pF, R = 1.5 k

3.2 Normal Working Condition

Symbol	Parameter	Min	Typ	Max	Unit
T_A	Temperature	-40	+25	+85	°C
H_A	Field strength	1.5		7.5	A/M

Table 3-2 FM11NT021TT normal working condition

3.3 Electrical characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_i	input frequency		13.553	13.56	13.567	MHz
C_i	input capacitance 【1】	Between IN1 and IN2		50		pF

Table 3-3 Electrical characteristics

【1】Measured with Agilent E5061B, the frequency is 13.56MHz, RMS voltage is 0.707V.

3.4 EEPROM characteristics

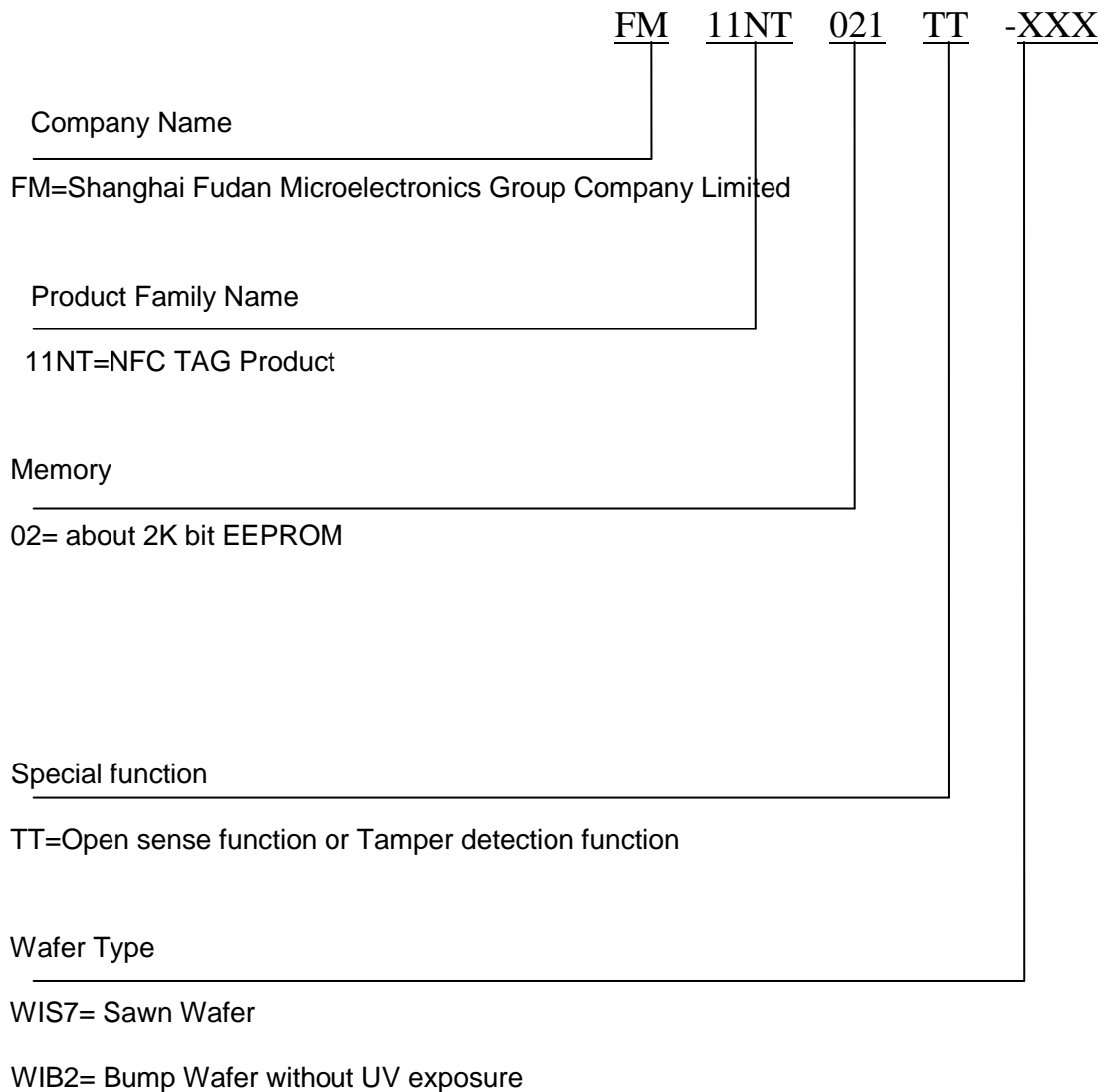| Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{ret}	retention time	$T_{amb} = 55℃$	10			year
$N_{endu(W)}$	write endurance	$T_{amb} = 25℃$	500000			cycle

Table 3-4 EEPROM characteristics

4 Ordering information

Type Number	Wafer Type	Description
FM11NT021TT-WIB2	Bump Sawn Wafer	8 inch bump wafer (120um thickness, without UV exposure, on film frame carrier; electronic fail die marking according to SECSII format)
FM11NT021TT-WIS7	Sawn Wafer	8 inch wafer (170 um thickness, on film frame carrier; electronic fail die marking according to SECSII format)

FM　11NT　021　TT　-XXX

Company Name

FM=Shanghai Fudan Microelectronics Group Company Limited

Product Family Name

11NT=NFC TAG Product

Memory

02= about 2K bit EEPROM

Special function

TT=Open sense function or Tamper detection function

Wafer Type

WIS7= Sawn Wafer

WIB2= Bump Wafer without UV exposure

Revision history

Version	Publication date	Pages	Paragraph or Illustration	Revise Description
1.0	Dec.2018	22		Initial release for the new version
1.1	Feb.2019	22		Ordering information updated
1.2	Nov.2022	20		Sales information updated

Sales and Service

Shanghai Fudan Microelectronics Group Co., Ltd.
Address: Bldg No. 4, 127 Guotai Rd, Shanghai City China.
Postcode: 200433
Tel: (86-021) 6565 5050 Fax: (86-021) 6565 9115

Shanghai Fudan Microelectronics (HK) Co., Ltd.
Address: Unit 506, 5/F., East Ocean Centre, 98 Granville Road, Tsimshatsui East, Kowloon, Hong Kong
Tel: (852) 2116 3288   2116 3338
Fax: (852) 2116 0882

Beijing Office
Address: Room 423, Bldg B, Gehua Building, 1 QingLong Hutong, Dongzhimen Alley north Street, Dongcheng District, Beijing City, China.
Postcode: 100007
Tel: (86-010) 8418 6608
Fax: (86-010) 8418 6211

Shenzhen Office
Address: Room.2306-2308, Building A7, Chuangzhi Cloud City, Liuxian Avenue, Xili Street, Nanshan District, Shenzhen, China.
Postcode: 518000
Tel: (86-0755) 8335 0911   8335 1011   8335 2011 8335 0611
Fax: (86-0755) 8335 9011

Shanghai Fudan Microelectronics (HK) Ltd Taiwan Representative Office
Address: Unit 1225, 12F., No 252, Sec.1 Neihu Rd., Neihu Dist., Taipei City 114, Taiwan
Tel : (886-2) 7721 1889
Fax: (886-2) 7722 3888

Shanghai Fudan Microelectronics (HK) Ltd Singapore Representative Office
Address : 47 Kallang Pudding Road, #08-06,The Crescent @ Kallang ,Singapore 349318
Tel : (65) 6443 0860
Fax: (65) 6443 1215

Fudan Microelectronics（USA）Inc.
Address : 97 E Brokaw Road, Suite 320,San Jose,CA 95112
Tel : (+1)408-335-6936

Web Site: http://www.fmsh.com/